Supporting Information

Toward Mechanically Stable Silicon-based Anodes using Si/SiO_x@C Hierarchical Structures with Well-controlled Internal Buffer Voids

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Figure S1 (A) N_2 sorption isotherms and (B) pore size distributions of the SSC-0, SSC-10 and SSC-60 composites.



Figure S2 Voltage profiles of pure sucrose-derived carbon electrode (A) and carbon-based electrode (B) obtained by etching the Si/SiO_x@C material (sintering the mixture of 20 wt% SiO and 80 wt% sucrose at 1100 °C for 5h under argon atmosphere).

Capactiy contriubtion $(mAh g^{-1})$	
r	
c	

Table S1 The conductivity values of different composites measured by 4-point probe

 method and the capacity contribution of different components

 Table S2 The comparison of initial charge-discharge capacity and capacity loss, energy density against graphite

Samples	Initial discharge capacity (mAh g ⁻¹)	Initial charge capacity (mAh g^{-1})	Initial irreversible capacity (mAh g^{-1})	Energy density (Wh kg ⁻¹)
Graphite	370	340	30	37.6 (100 th)
SSC-0	1282.1	828.5	453.6	$50.3(100^{th})$
SSC-10	1618.6	1209.1	409.5	191.2(100 th)
SSC-60	734.6	430.7	303.9	95.6(100 th)
BSSC-10	1507.2	1058.3	448.9	$162(100^{th})$